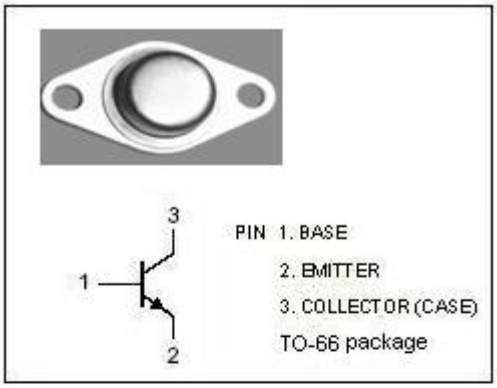
isc Silicon NPN Power Transistor 2SC1450

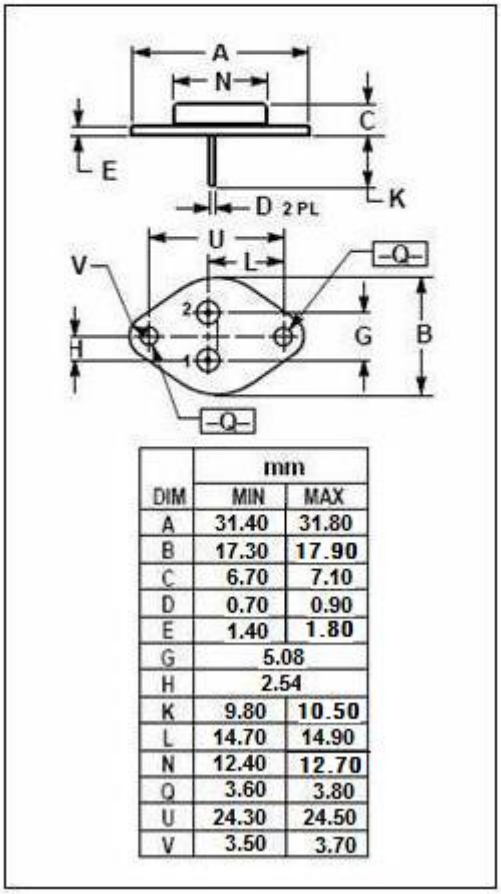
DESCRIPTION

- With TO-66 Package
- Low collector saturation voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.



APPLICATIONS

- Designed for switching and wide-band amplifier applications



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.4	A
P_C	Collector Power Dissipation @ T_C=25℃	20	W
T_J	Junction Temperature	-65~150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	6.25	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B= 50mA		1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 150V;I_B= 0		10	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C=0		10	uA
h_{FE}	DC Current Gain	I_C= 0.1A ; V_{CE}= 5V	30	150	